Printed Pages-3	Roll No			[2]	
			(c)	Write short notes on:	7
				(i) Velocity overshoot	
				(ii) Electron mobility	
32			(iii) Critical thickness.		
B. E. (Seventh Semester) Examination, April-May 2020			` ′	What is band gap discontinuity and band gap narrowing explain briefly.	7
(Old Scheme)		Unit-II			
(EEE, Et & T Engg. Branch) ADVANCED SOLID STATE DEVICES Time Allowed: Three hours		2.	(a)	What is HBTs.	2
			(b)]	Explain the operation of High Electron Mobility	,
			transistors with neat diagram. (HEMTs).		7
Maximum Marks : 80 Minimum Pass Marks : 28			(c)	What are the difference between single electron	l
				transistor & velocity modulated transistor.	7
Note: Attempt all questions. Part (a) of each question is compulsory and carries 2 marks and attempt two parts from (b), (c) and (d) and carry 7 marks each.			(d)	Write short notes on:	7
				(i) Resonant Tunneling Diodes	
				(ii) Heterostructure FET. (HFETs)	
·	Unit-I			Unit-III	
1. (a) What is semiconductors. 2		3.	(a) What is Schottky barrier.		2

(b) Explain band gaps & lattice constants with diagram. 7 PTO

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(b) Describe the NMOS fabrication process with

suitable diagram.

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	(c)	Explain the operation of CMOS with its VTC.	7					
	(d)	Draw and explain small signal parameters and equivalent circuit of MOSFET.	7					
Unit-IV								
4.	(a)	What is Lasers.	2					
	(b)	Explain Absorption Losses mechanism associated with optical fiber.	7					
	(c)	What are different types of Lasers? Explain their briefly.	7					
	(d)	Explain the operation of PIN photo diode with neat diagram.	7					
Unit-V								
5.	(a)	What is the use of switched capacitor filters.	2					
	(b)	Compare different types of OTA.	7					
	(c)	Explain the operation of LMF100 switched capacitor filter.	7					
	(d)	Explain briefly the operation of the operational trans- conductance Amplifier (OTA).	7					